

85V N-Channel Enhancement Mode MOSFET

Description

The AP180N08P/T uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 10V.

This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 85V$ $I_D = 180A$

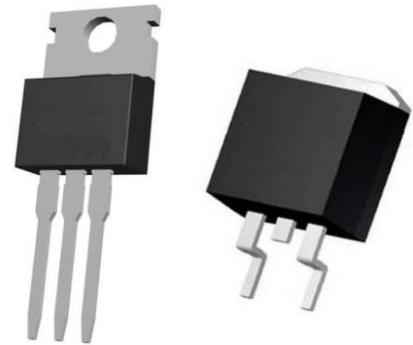
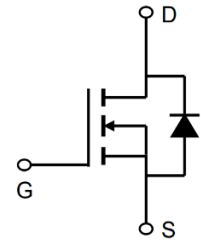
$R_{DS(ON)} < 3.5m\Omega$ $V_{GS}=10V$ (Type: 2.9m Ω)

Application

Battery protection

Load switch

Uninterruptible power supply



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AP180N08P	TO-220-3L	AP180N08P XXX YYYY	1000
AP180N08T	TO-263-3L	AP180N08T XXX YYYY	800

Absolute Maximum Ratings ($T_C=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	85	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V$	180	A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V$	100	A
IDM	Pulsed Drain Current	480	A
EAS	Single Pulse Avalanche Energy	858	mJ
$P_D@T_C=25^{\circ}C$	Total Power Dissipation ⁴	284	W
TSTG	Storage Temperature Range	-55 to 150	$^{\circ}C$
T_J	Operating Junction Temperature Range	-55 to 150	$^{\circ}C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	0.53	$^{\circ}C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case	48	$^{\circ}C/W$

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Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V(BR)DSS	Drain-source breakdown voltage	$V_{GS}=0V, I_D=250\mu A$	85	92		V
VGS(th)	Gate threshold voltage	$V_{DS}=V_{GS}, I_D=250\mu A, T_J=25^\circ\text{C}$	2.0	3.0	4.0	V
IDSS	Zero gate voltage drain current	$V_{DS}=80V, V_{GS}=0V, T_J=25^\circ\text{C}$	-		1	μA
IDSS	Zero gate voltage drain current	$V_{DS}=80V, V_{GS}=0V, T_J=125^\circ\text{C}$		- 5		μA
IGSS	Gate-source leakage current	$V_{GS}=20V, V_{DS}=0V$	-	-	100	nA
RDS(on)	Drain-source on-state resistance	$V_{GS}=10V, I_D=50A, T_J=25^\circ\text{C}$	-	2.9	3.5	m Ω
gfs	Transconductance	$V_{DS}=5V, I_D=40A$	-	106	-	S
Ciss	Input Capacitance	$V_{GS}=0V, V_{DS}=40V, f=1\text{MHz}$	-	6813	-	pF
Coss	Output Capacitance		-	808	-	pF
Crss	Reverse Transfer Capacitance		-	48	-	pF
Qg	Gate Total Charge	$V_{GS}=10V, V_{DS}=40V, I_D=25A$	-	91	-	nC
Qgs	Gate-Source charge		-	37	-	nC
Qgd	Gate-Drain charge		-	25	-	nC
td(on)	Turn-on delay time	$T_J=25^\circ\text{C}, V_{GS}=10V, V_{DS}=40V, R_L=3\Omega$	-	38	-	ns
t _r	Rise time		-	58	-	ns
td(off)	Turn-off delay time		-	63	-	ns
t _f	Fall time		-	32	-	ns
R _G	Gate resistance	$V_{GS}=0V, V_{DS}=0V, f=1\text{MHz}$	-	2	-	Ω
VSD	Body Diode Forward Voltage	$V_{GS}=0V, I_{SD}=50A$	-	0.85	1.2	V
trr	Body Diode Reverse Recovery Time	$I_F=20A, dI/dt=500A/\mu s$	-	85	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	313	-	nC

Note :

- 1、The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width .The EAS data shows Max. rating .
- 3、The test cond \cong 300us duty cycle \cong 2%, duty cycle ition is $V_{DD}=64V, V_{GS}=10V, L=0.1\text{mH}, I_{AS}=53.8A$
- 4、The power dissipation is limited by 175 $^\circ\text{C}$ junction temperature
- 5、The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

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Typical Characteristics

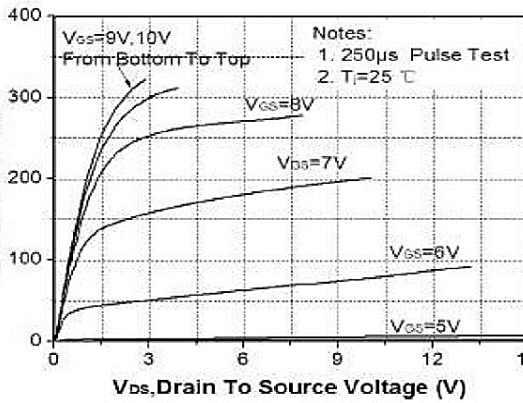


Figure 1. Typ. Output Characteristics (Tj=25 °C)

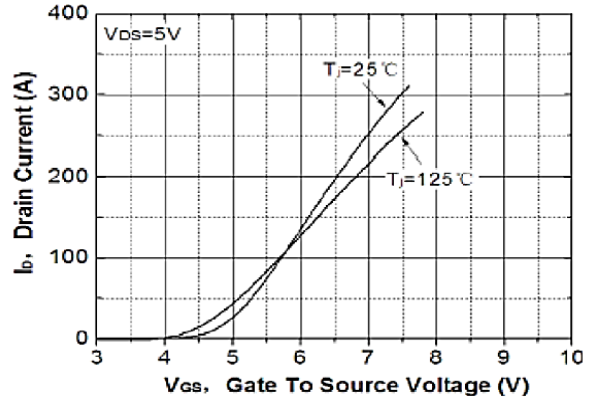


Figure 2. Transfer Characteristics

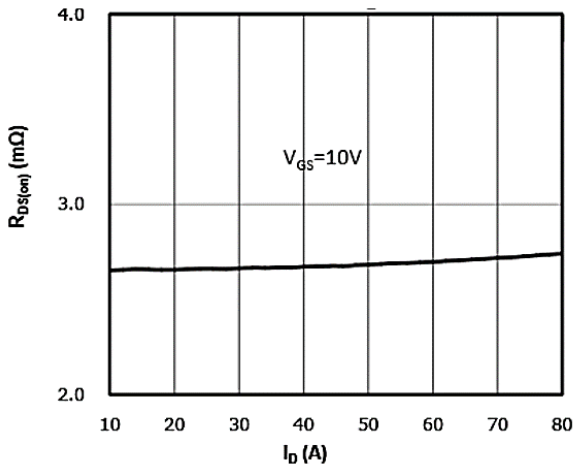


Figure 3. On-Resistance vs. Drain Current and Gate Voltage Figure

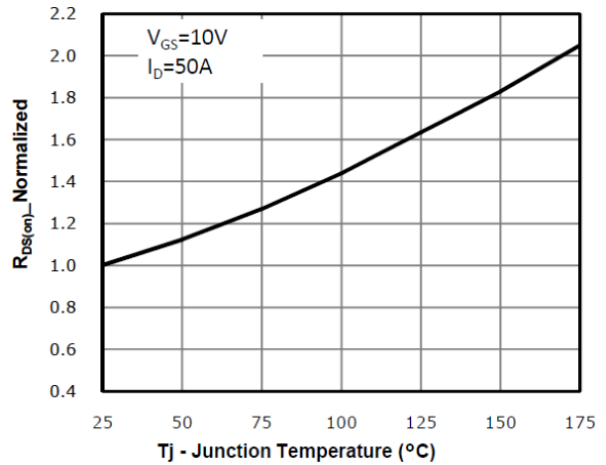


Figure 4. On-Resistance vs. Junction Temperature

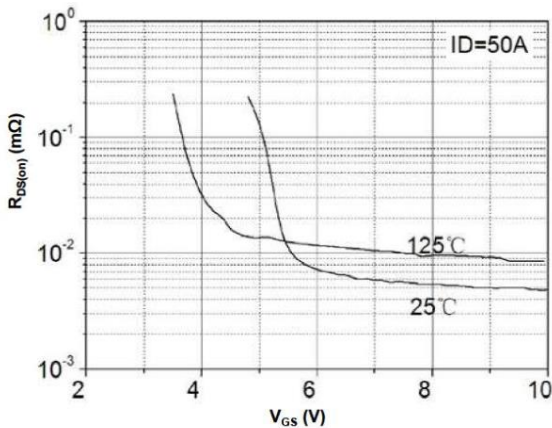


Figure 5. On-Resistance vs. Gate-Source Voltage

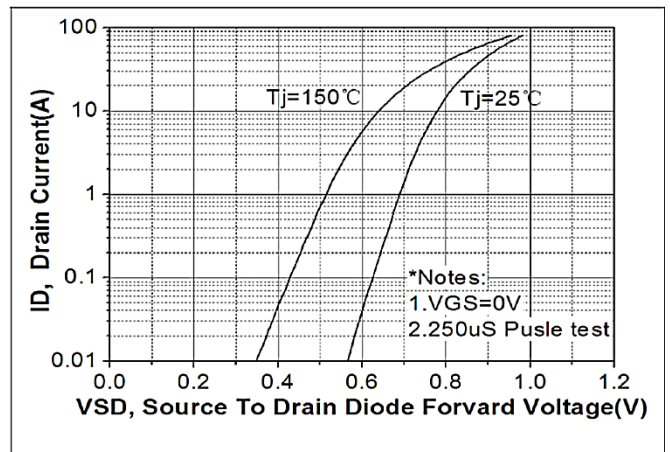


Figure 6. Body-Diode Characteristics

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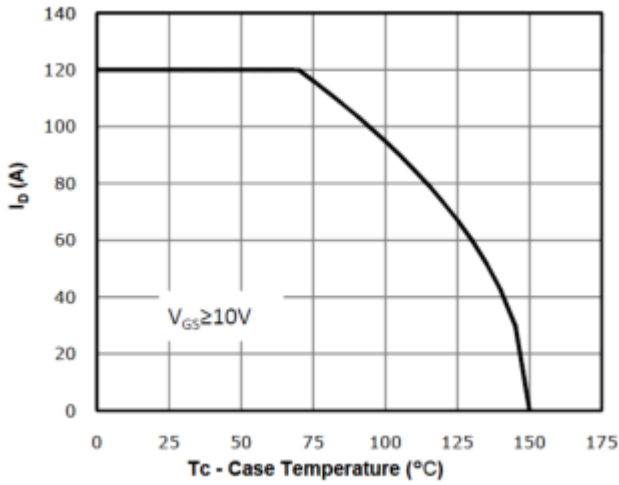


Figure 7. Gate-Charge Characteristics

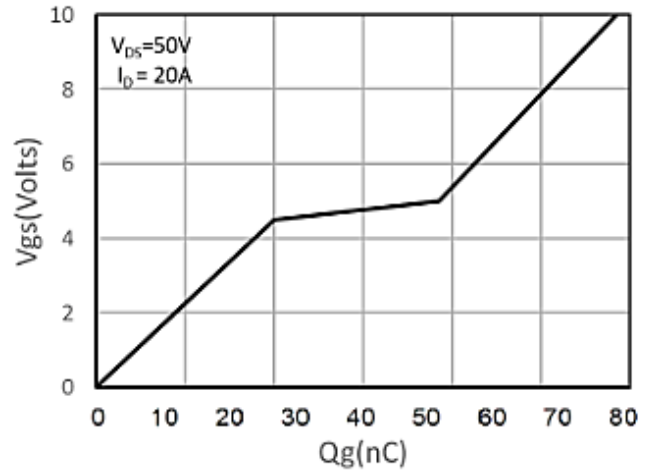


Figure 8. Drain Current Derating

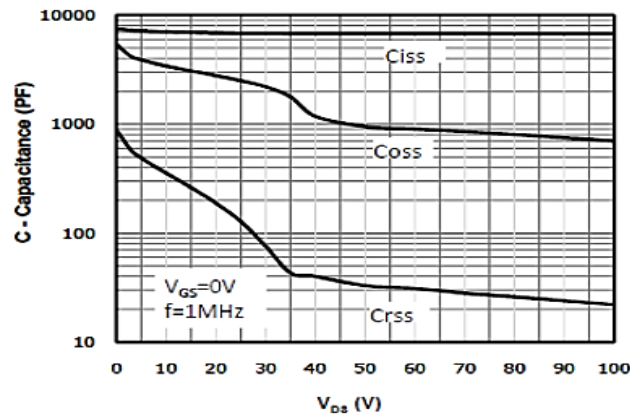


Figure 9: Normalized Maximum Transient Thermal Impedance

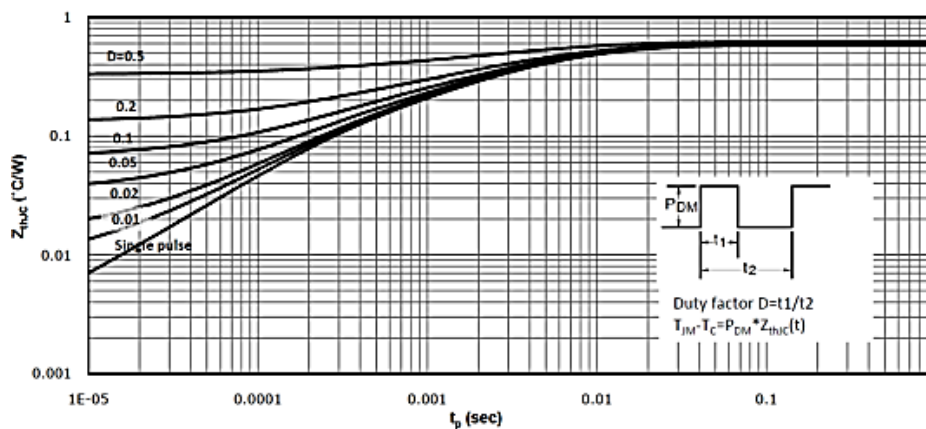
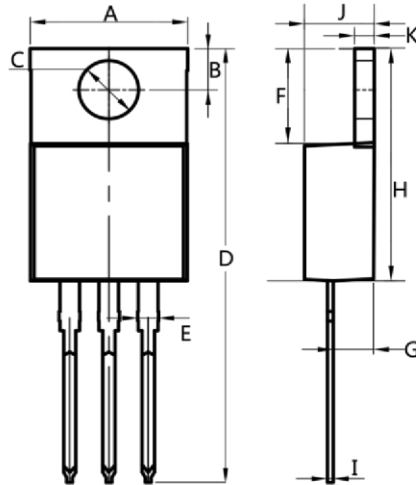


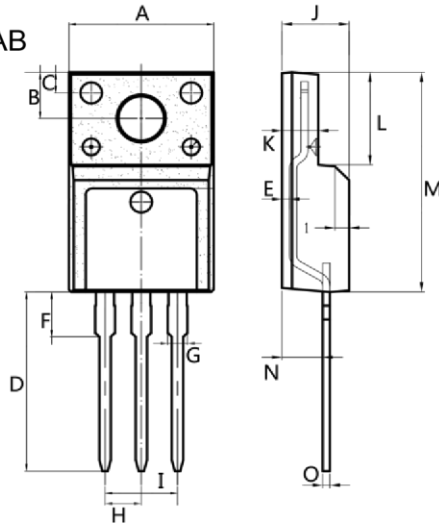
Figure 10. Capacitance Characteristics

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TO-220AB


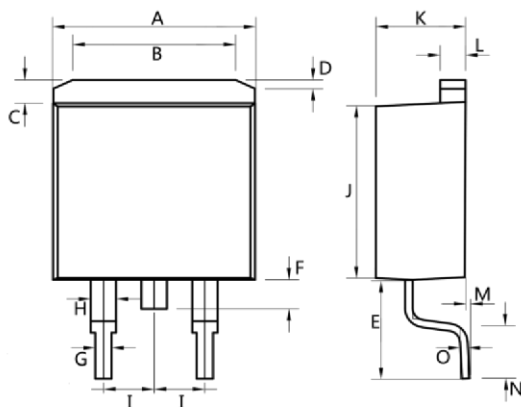
Dim.	Min.	Max.
A	10.0	10.4
B	2.5	3.0
C	3.5	4.0
D	28.0	30.0
E	1.1	1.5
F	6.2	6.6
G	2.9	3.3
H	15.0	16.0
I	0.35	0.45
J	4.3	4.7
K	1.2	1.4

All Dimensions in millimeter

ITO-220AB


Dim.	Min.	Max.
A	9.9	10.3
B	2.9	3.5
C	1.15	1.45
D	12.75	13.25
E	0.55	0.75
F	3.1	3.5
G	1.25	1.45
H	Typ 2.54	
I	Typ 5.08	
J	4.55	4.75
K	2.4	2.7
L	6.35	6.75
M	15.0	16.0
N	2.75	3.15
O	0.45	0.60

All Dimensions in millimeter

TO-263


Dim.	Min.	Max.
A	10.0	10.5
B	7.25	7.75
C	1.3	1.5
D	0.55	0.75
E	5.0	6.0
F	1.4	1.6
G	0.75	0.95
H	1.15	1.35
I	Typ 2.54	
J	8.4	8.6
K	4.4	4.6
L	1.25	1.45
M	0.02	0.1
N	2.4	2.8
O	0.35	0.45

All Dimensions in millimeter